Akinobu Teramoto

List of Publications by Year
in descending order

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274
papers

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276
times ranked

1180
citing authors

#	Article	IF	Citations
1	High Permeability and Low Loss Niâ€“Fe Composite Material for High-Frequency Applications. IEEE Transactions on Magnetics, 2008, 44, 2100-2106.	2.1	94
2	New era of silicon technologies due to radical reaction based semiconductor manufacturing. Journal Physics D: Applied Physics, 2006, 39, R1-R17.	2.8	88
3	Very High Carrier Mobility for High-Performance CMOS on a Si(110) Surface. IEEE Transactions on Electron Devices, 2007, 54, 1438-1445.	3.0	70
4	Atomically Flat Silicon Surface and Silicon/Insulator Interface Formation Technologies for (100) Surface Orientation Large-Diameter Wafers Introducing High Performance and Low-Noise Metalâ€“Insulatorâ€“Silicon FETs. IEEE Transactions on Electron Devices, 2009, 56, 291-298.	3.0	59
5	Model for the substrate hole current based on thermionic hole emission from the anode during Fowlerâ€“Nordheim electron tunneling innâ€channel metalâ€oxideâ€semiconductor fieldâ€effect transistors. Journal of Applied Physics, 1995, 77, 3277-3282.	2.5	53
6	Impact of Improved High-Performance Si(110)-Oriented Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors Using Accumulation-Mode Fully Depleted Silicon-on-Insulator Devices. Japanese Journal of Applied Physics, 2006, 45, 3110-3116.	1.5	50
7	Revolutional Progress of Silicon Technologies Exhibiting Very High Speed Performance Over a 50-GHz Clock Rate. IEEE Transactions on Electron Devices, 2007, 54, 1471-1477.	3.0	45
8	1/f noise suppression of pMOSFETs fabricated on Si(100) and Si(110) using an alkali-free cleaning process. IEEE Transactions on Electron Devices, 2006, 53, 851-856.	3.0	44
9	High Quality SiO₂/Al₂O₃ Gate Stack for GaN Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor. Japanese Journal of Applied Physics, 2013, 52, 04CF09.	1.5	37
10	High-Speed Damage-Free Contact Hole Etching Using Dual Shower Head Microwave-Excited High-Density-Plasma Equipment. Japanese Journal of Applied Physics, 2004, 43, 1784-1787.	1.5	34
11	Native Oxide Growth on Silicon Surface in Ultrapure Water and Hydrogen Peroxide. Japanese Journal of Applied Physics, 1990, 29, L2392-L2394.	1.5	33
12	High-Quality Silicon Oxide Film Formed by Diffusion Region Plasma Enhanced Chemical Vapor Deposition and Oxygen Radical Treatment Using Microwave-Excited High-Density Plasma. Japanese Journal of Applied Physics, 2003, 42, 1911-1915.	1.5	31
13	Stable yttrium oxyfluoride used in plasma process chamber. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	2.1	29
14	Random Telegraph Signal Statistical Analysis using a Very Large-scale Array TEG with 1M MOSFETs. , 2007, , .		28
15	Complementary Metalâ€“Oxideâ€“Silicon Field-Effect-Transistors Featuring Atomically Flat Gate Insulator Film/Silicon Interface. Japanese Journal of Applied Physics, 2009, 48, 04C048.	1.5	28
16	Atomically Flattening Technology at 850Â°C for Si(100) Surface. ECS Transactions, 2010, 28, 299-309.	0.5	28
17	New Statistical Evaluation Method for the Variation of Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2007, 46, 2054-2057.	1.5	27
18	Effect of Additives in Organic Acid Solutions for Post-CMP Cleaning on Polymer Low-k Fluorocarbon. Journal of the Electrochemical Society, 2009, 156, H409.	2.9	26

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19	Understanding of traps causing random telegraph noise based on experimentally extracted time constants and amplitude. , 2011, , .		26
20	Statistical analysis of Random Telegraph Noise reduction effect by separating channel from the interface. , 2012, , .		25
21	A Statistical Evaluation of Random Telegraph Noise of In-Pixel Source Follower Equivalent Surface and Buried Channel Transistors. IEEE Transactions on Electron Devices, 2013, 60, 3555-3561.	3.0	25
22	Electron Traps and Excess Current Induced by Hotâ€Hole Injection into Thin SiO2 Films. Journal of the Electrochemical Society, 1996, 143, 3377-3383.	2.9	24
23	Relation Between the Mobility, $hbox{1}/f$ Noise, and Channel Direction in MOSFETs Fabricated on (100) and (110) Silicon-Oriented Wafers. IEEE Transactions on Electron Devices, 2010, 57, 1597-1607.	3.0	24
24	A Technology for Reducing Flicker Noise for ULSI Applications. Japanese Journal of Applied Physics, 2003, 42, 2106-2109.	1.5	23
25	Hydrogen termination of Si(110) surfaces upon wet cleaning revealed by highly resolved scanning tunneling microscopy. Journal of Applied Physics, 2005, 98, 103525.	2.5	22
26	Preoxide-Controlled Oxidation for Very Thin Oxide Films. Japanese Journal of Applied Physics, 1993, 32, 294-297.	1.5	21
27	XPS Study of H-Terminated Silicon Surface under Inert Gas and UHV Annealing. Journal of the Electrochemical Society, 2005, 152, G163.	2.9	21
28	Large-Scale Test Circuits for High-Speed and Highly Accurate Evaluation of Variability and Noise in Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor Electrical Characteristics. Japanese Journal of Applied Physics, 2011, 50, 106701.	1.5	21
29	Reduction of Scratch on Brush Scrubbing in Post CMP Cleaning by Analyzing Contact Kinetics on Ultra Low-k Dielectric. ECS Transactions, 2009, 19, 103-109.	0.5	20
30	End-Point Detection of Ta/TaN Chemical Mechanical Planarization via Forces Analysis. Japanese Journal of Applied Physics, 2010, 49, 05FC01.	1.5	20
31	GEOMETRY AND BIAS DEPENDENCE OF LOW-FREQUENCY RANDOM TELEGRAPH SIGNAL AND 1/f NOISE LEVELS IN MOSFETS. Fluctuation and Noise Letters, 2005, 05, L539-L548.	1.5	19
32	Subnitride and valence band offset at Si3N4â^•Si interface formed using nitrogen-hydrogen radicals. Applied Physics Letters, 2007, 90, 123114.	3.3	19
33	Experimental Investigation of Effect of Channel Doping Concentration on Random Telegraph Signal Noise. Japanese Journal of Applied Physics, 2010, 49, 04DC07.	1.5	19
34	Origin of positive charge generated in thin SiO/sub 2/ films during high-field electrical stress. IEEE Transactions on Electron Devices, 1999, 46, 947-953.	3.0	18
35	Low-Dielectric-Constant Nonporous Fluorocarbon Films for Interlayer Dielectric. Japanese Journal of Applied Physics, 2008, 47, 2515-2520.	1.5	18
36	Low-Loss Composite Material Containing Fine Znâ€“Niâ€“Fe Flakes for High-Frequency Applications. IEEE Transactions on Magnetics, 2009, 45, 4337-4340.	2.1	18

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37	Modelling of the hole mobility in p-channel MOS transistors fabricated on (1 1 0) oriented silicon wafers. Solid-State Electronics, 2010, 54, 420-426.	1.4	18
38	Very Low Bit Error Rate in Flash Memory Using Tunnel Dielectrics Formed by Kr/O2/NO Plasma Oxynitridation. Japanese Journal of Applied Physics, 2007, 46, 2148-2152.	1.5	17
39	Characterization of MgZnO films grown by plasma enhanced metal-organic chemical vapor deposition. Thin Solid Films, 2010, 518, 2953-2956.	1.8	17
40	Time-dependent dielectric breakdown of SiO2 films in a wide electric field range. Microelectronics Reliability, 2001, 41, 47-52.	1.7	16
41	Effect of Silicon WaferIn SituCleaning on the Chemical Structure of Ultrathin Silicon Oxide Film. Japanese Journal of Applied Physics, 1991, 30, 3584-3589.	1.5	15
42	Angle resolved X-ray photoelectron spectroscopic study of ultrathin oxynitrides. Materials Science in Semiconductor Processing, 1999, 2, 225-231.	4.0	15
43	Analyzing correlation between multiple traps in RTN characteristics. , 2014, , .		15
44	High performance and highly reliable novel CMOS devices using accumulation mode multi-gate and fully depleted SOI MOSFETs. Microelectronic Engineering, 2007, 84, 2105-2108.	2.4	14
45	Angle-resolved photoelectron study on the structures of silicon nitride films and Si3N4/Si interfaces formed using nitrogen-hydrogen radicals. Journal of Applied Physics, 2008, 104, .	2.5	14
46	Formation and Property of Yttrium and Yttrium Silicide Films as Low Schottcky Barrier material for n-Type Silicon. Japanese Journal of Applied Physics, 2008, 47, 3138.	1.5	14
47	In situObservation of Grain Growth on Electroplated Cu Film by Electron Backscatter Diffraction. Japanese Journal of Applied Physics, 2009, 48, 066507.	1.5	14
48	Formation speed of atomically flat surface on Si (100) in ultra-pure argon. Microelectronic Engineering, 2011, 88, 3133-3139.	2.4	14
49	The electric properties of low-magnetic-loss magnetic composites containing Znâ€"Niâ€"Fe particles. Journal of Physics Condensed Matter, 2009, 21, 436009.	1.8	13
50	Different mechanism to explain the 1â^•f noise in n- and p-SOI-MOS transistors fabricated on (110) and (100) silicon-oriented wafers. Journal of Vacuum Science & Technology B, 2009, 27, 394-401.	1.3	13
51	Tribological Study of Brush Scrubbing in Post-Chemical Mechanical Planarization Cleaning in Non-porous Ultralow-k Dielectricâ^•Cu Interconnects. Journal of the Electrochemical Society, 2011, 158, H1145.	2.9	13
52	Densification of chemical vapor deposition silicon dioxide film using oxygen radical oxidation. Journal of Applied Physics, 2012, 111, 034101.	2.5	13
53	The study of time constant analysis in random telegraph noise at the subthreshold voltage region. , 2013, , .		13
54	Extraction of time constants ratio over nine orders of magnitude for understanding random telegraph noise in metalâ€"oxideâ€"semiconductor field-effect transistors. Japanese Journal of Applied Physics, 2014, 53, 04EC19.	1.5	13

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55	Influence of silicon wafer surface roughness on semiconductor device characteristics. Japanese Journal of Applied Physics, 2020, 59, SMMB06.	1.5	13
56	Highly Reliable SiO2Films Formed by UV-O2Oxidation. Japanese Journal of Applied Physics, 1998, 37, 1122-1124.	1.5	12
57	Effects of N distribution on charge trapping and TDDB characteristics of N/sub 2/O annealed wet oxide. IEEE Transactions on Electron Devices, 1999, 46, 1121-1126.	3.0	12
58	Precise Control of Nitrogen Profiles and Nitrogen Bond States for Highly Reliable N[sub 2]O-Grown Oxynitride. Journal of the Electrochemical Society, 2000, 147, 1888.	2.9	12
59	Anomalous Random Telegraph Signal Extractions from a Very Large Number of n-Metal Oxide Semiconductor Field-Effect Transistors Using Test Element Groups with 0.47 Hzâ€“3.0 MHz Sampling Frequency. Japanese Journal of Applied Physics, 2009, 48, 04C044.	1.5	12
60	A Test Structure for Statistical Evaluation of Characteristics Variability in a Very Large Number of MOSFETs. , 2009, , .		12
61	Statistical Evaluation of Process Damage Using an Arrayed Test Pattern in a Large Number of MOSFETs. IEEE Transactions on Electron Devices, 2010, 57, 1310-1318.	3.0	12
62	Analysis of Hundreds of Time Constant Ratios and Amplitudes of Random Telegraph Signal with Very Large Scale Array Test Pattern. Japanese Journal of Applied Physics, 2010, 49, 04DC06.	1.5	12
63	Low Leakage Current Al2O3 Metal-Insulator-Metal Capacitors Formed By Atomic Layer Deposition at Optimized Process Temperature and O2 Post Deposition Annealing. ECS Transactions, 2016, 72, 91-100.	0.5	12
64	Random telegraph noise measurement and analysis based on arrayed test circuit toward high S/N CMOS image sensors. , 2016, , .		12
65	Charge Transport in Ultrathin Silicon Nitrides. Journal of the Electrochemical Society, 1995, 142, 990-996.	2.9	11
66	Accurate Time Constant of Random Telegraph Signal Extracted by a Sufficient Long Time Measurement in Very Large-Scale Array TEG. , 2009, , .		10
67	Asymmetry of RTS characteristics along source-drain direction and statistical analysis of process-induced RTS. , 2009, , .		10
68	Statistical evaluation for trap energy level of RTS characteristics. , 2010, , .		10
69	High-Rate Deposition of Amorphous Silicon Films by Microwave-Excited High-Density Plasma. Japanese Journal of Applied Physics, 2011, 50, 036502.	1.5	10
70	Damage-Free Post-CMP Cleaning Solution for Low-<i>k</i> Fluorocarbon on Advanced Interconnects. Solid State Phenomena, 2009, 145-146, 381-384.	0.3	9
71	Very High Performance CMOS on Si(551) Using Radical Oxidation Technology and Accumulation-Mode SOI Device Structure. Journal of the Electrochemical Society, 2010, 157, H389.	2.9	9
72	Tribological Effects of Brush Scrubbing in Post Chemical Mechanical Planarization Cleaning on Electrical Characteristics in Novel Non-porous Low-kDielectric Fluorocarbon on Cu Interconnects. Japanese Journal of Applied Physics, 2011, 50, 05EC07.	1.5	9

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73	Low-Interface-Trap-Density and High-Breakdown-Electric-Field SiN Films on GaN Formed by Plasma Pretreatment Using Microwave-Excited Plasma-Enhanced Chemical Vapor Deposition. IEEE Transactions on Electron Devices, 2013, 60, 1916-1922.	3.0	9
74	Chemical Structure of Interfacial Transition Layer Formed on Si(100) and Its Dependence on Oxidation Temperature, Annealing in Forming Gas, and Difference in Oxidizing Species. Japanese Journal of Applied Physics, 2013, 52, 031302.	1.5	9
75	Atomically flattening of Si surface of silicon on insulator and isolation-patterned wafers. Japanese Journal of Applied Physics, 2015, 54, 04DA04.	1.5	9
76	X-ray photoelectron spectroscopy study of dielectric constant for Si compounds. Applied Physics Letters, 2006, 89, 154103.	3.3	8
77	Lattice Distortion at SiO2/Si(001) Interface Studied with High-Resolution Rutherford Backscattering Spectroscopy/Channeling. Japanese Journal of Applied Physics, 2006, 45, 2467-2469.	1.5	8
78	The Influence of Interconnect Line Patterns using Flat-Surface and Low-Dielectric-Loss Material under High Speed Signal Propagation. , 2007, , .		8
79	High-Efficiency PFC Abatement System Utilizing Plasma Decomposition and Ca(OH)$_{2}$/CaO Immobilization. IEEE Transactions on Semiconductor Manufacturing, 2008, 21, 668-675.	1.7	8
80	Three-Step Room-Temperature Cleaning of Bare Silicon Surface for Radical-Reaction-Based Semiconductor Manufacturing. Journal of the Electrochemical Society, 2009, 156, H10.	2.9	8
81	Impact of Tungsten Capping Layer on Yttrium Silicide for Low-Resistance n+-Source/Drain Contacts. Japanese Journal of Applied Physics, 2009, 48, 04C046.	1.5	8
82	Effect of Various Cleaning Solutions and Brush Scrubber Kinematics on the Frictional Attributes of Post Copper CMP Cleaning Process. Solid State Phenomena, 0, 145-146, 363-366.	0.3	8
83	Crystallographic orientation dependence of compositional transition and valence band offset at SiO2/Si interface formed using oxygen radicals. Applied Physics Letters, 2010, 96, 173103.	3.3	8
84	Low Contact Resistivity with Low Silicide/p+-Silicon Schottky Barrier for High-Performance p-Channel Metalâ€“Oxideâ€“Silicon Field Effect Transistors. Japanese Journal of Applied Physics, 2010, 49, 04DA03.	1.5	8
85	Depth Profile of Nitrogen Atoms in Silicon Oxynitride Films Formed by Low-Electron-Temperature Microwave Plasma Nitridation. Japanese Journal of Applied Physics, 2010, 49, 091301.	1.5	8
86	Evaluation for Anomalous Stress-Induced Leakage Current of Gate $ hbox{SiO}_{2}$ Films Using Array Test Pattern. IEEE Transactions on Electron Devices, 2011, 58, 3307-3313.	3.0	8
87	Visualization of Single Atomic Steps on An Ultra-Flat Si(100) Surface by Advanced Differential Interference Contrast Microscopy. Electrochemical and Solid-State Letters, 2011, 14, H351.	2.2	8
88	Hole Mobility in Accumulation Mode Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2012, 51, 04DC07.	1.5	8
89	Clarification of Nitridation Effect on Oxide Formation Methods. Japanese Journal of Applied Physics, 1996, 35, 1454-1459.	1.5	7
90	Dielectric breakdown caused by hole-induced-defect in thin SiO2 films. Applied Surface Science, 1997, 117-118, 245-248.	6.1	7

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91	Electric Characteristics of Si3N4Films Formed by Directly Radical Nitridation on Si(110) and Si(100) Surfaces. Japanese Journal of Applied Physics, 2007, 46, 1895-1898.	1.5	7
92	Hot Carrier Instability Mechanism in Accumulation-Mode Normally-off SOI nMOSFETs and Their Reliability Advantage. ECS Transactions, 2007, 6, 113-118.	0.5	7
93	Nitrogen Profile Study for SiON Gate Dielectrics of Advanced Dynamic Random Access Memory. Japanese Journal of Applied Physics, 2008, 47, 5380.	1.5	7
94	Advanced Method for Measuring Ultra-Low Contact Resistivity Between Silicide and Silicon Based on Cross Bridge Kelvin Resistor. , 2009, , .		7
95	High-Frequency Propagation on Printed Circuit Board Using a Material With a Low Dielectric Constant, a Low Dielectric Loss, and a Flat Surface. IEEE Transactions on Components and Packaging Technologies, 2009, 32, 415-423.	1.3	7
96	Electrical Characteristics of Novel Non-porous Low-kDielectric Fluorocarbon on Cu Interconnects for 22 nm Generation and Beyond. Japanese Journal of Applied Physics, 2011, 50, 05EB02.	1.5	7
97	High Integrity SiO$_{2}$ Gate Insulator Formed by Microwave-Excited Plasma Enhanced Chemical Vapor Deposition for AlGaN/GaN Hybrid Metalâ€"Oxideâ€"Semiconductor Heterojunction Field-Effect Transistor on Si Substrate. Japanese Journal of Applied Physics, 2012, 51, 04DF03.	1.5	7
98	Evaluation of Low-Frequency Noise in MOSFETs Used as a Key Component in Semiconductor Memory Devices. Electronics (Switzerland), 2021, 10, 1759.	3.1	7
99	Ferroelectric Sr2(Ta1-x, Nbx)2O7with a Low Dielectric Constant by Plasma Physical Vapor Deposition and Oxygen Radical Treatment. Japanese Journal of Applied Physics, 2003, 42, 2050-2054.	1.5	6
100	Capacitanceâ€"Voltage Measurement Method for Ultrathin Gate Dielectrics Using LC Resonance Circuit. IEEE Transactions on Semiconductor Manufacturing, 2006, 19, 43-49.	1.7	6
101	Characterization of Zinc Oxide Films Grown by a Newly Developed Plasma Enhanced Metal Organic Chemical Vapor Deposition Employing Microwave Excited High Density Plasma. Japanese Journal of Applied Physics, 2008, 47, 2994-2998.	1.5	6
102	Performance Comparison of Ultrathin Fully Depleted Silicon-on-Insulator Inversion-, Intrinsic-, and Accumulation-Mode Metalâ€"Oxideâ€"Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2008, 47, 2668-2671.	1.5	6
103	Damage-free microwave-excited plasma etching without carrier deactivation of heavily doped Si under thin silicide layer. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 8-16.	2.1	6
104	Analysis of the Low-Frequency Noise Reduction in Si(100) Metalâ€"Oxideâ€"Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 04DC01.	1.5	6
105	Gate SiO2 Film Integrity on Ultra-Pure Argon Anneal (100) Silicon Surface. ECS Transactions, 2011, 41, 147-156.	0.5	6
106	1/f CHANNEL NOISE AT HIGH DRAIN CURRENT IN MOS TRANSISTORS. Fluctuation and Noise Letters, 2011, 10, 431-445.	1.5	6
107	Demonstrating distribution of SILC values at individual leakage spots. , 2013, , .		6
108	Low Interface Trap Density and High Breakdown Electric Field SiN Films on GaN Formed by Plasma Pretreatment Using Microwave-Excited Plasma-Enhanced Chemical Vapor Deposition. IEEE Transactions on Electron Devices, 2016, 63, 1795-1801.	3.0	6

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109	Statistical evaluation for anomalous SILC of tunnel oxide using integrated array TEG. , 2008, , .		5
110	Stress-induced leakage current and random telegraph signal. Journal of Vacuum Science & Technology B, 2009, 27, 435.	1.3	5
111	Novel End-point Detection Method by Monitoring Shear Force Oscillation Frequency for Barrier Metal Polishing in Advanced LSI. Materials Research Society Symposia Proceedings, 2009, 1157, 1.	0.1	5
112	Experimental demonstration and analysis of high performance and low 1/f noise Tri-gate MOSFETs by optimizing device structure. Microelectronic Engineering, 2009, 86, 1786-1788.	2.4	5
113	Characterization for High-Performance CMOS Using In-Wafer Advanced Kelvin-Contact Device Structure. IEEE Transactions on Semiconductor Manufacturing, 2009, 22, 126-133.	1.7	5
114	Light-Emitting Diode Based on ZnO by Plasma-Enhanced Metalâ€"Organic Chemical Vapor Deposition Employing Microwave Excited Plasma. Japanese Journal of Applied Physics, 2010, 49, 04DG14.	1.5	5
115	Highly Reliable Radical SiO₂Films on Atomically Flat Silicon Surface Formed by Low Temperature Pure Ar Annealing. Japanese Journal of Applied Physics, 2011, 50, 10PB05.	1.5	5
116	Advanced Direct-Polish Process on Organic Non-Porous Ultra Low-k Fluorocarbon Dielectric on Cu Interconnects. ECS Transactions, 2011, 34, 653-658.	0.5	5
117	Advanced Direct-Polishing Process Development of Non-Porous Ultralow-<i>k</i>Dielectric Fluorocarbon with Plasma Treatment on Cu Interconnects. Journal of the Electrochemical Society, 2012, 159, H407-H411.	2.9	5
118	A Simple Test Structure for Evaluating the Variability in Key Characteristics of a Large Number of MOSFETs. IEEE Transactions on Semiconductor Manufacturing, 2012, 25, 145-154.	1.7	5
119	Cu Single Damascene Integration of an Organic Nonporous Ultralow- k Fluorocarbon Dielectric Deposited by Microwave-Excited Plasma-Enhanced CVD. IEEE Transactions on Electron Devices, 2012, 59, 1445-1453.	3.0	5
120	Structural Analyses of Thin SiO₂Films Formed by Thermal Oxidation of Atomically Flat Si Surface by Using Synchrotron Radiation X-Ray Characterization. ECS Journal of Solid State Science and Technology, 2015, 4, N96-N98.	1.8	5
121	Introduction of Atomically Flattening of Si Surface to Large-Scale Integration Process Employing Shallow Trench Isolation. ECS Journal of Solid State Science and Technology, 2016, 5, P67-P72.	1.8	5
122	Performances of accumulation-mode n- and p-MOSFETs on Si(110) wafers. Japanese Journal of Applied Physics, 2017, 56, 04CD15.	1.5	5
123	[Papers] Statistical Analyses of Random Telegraph Noise in Pixel Source Follower with Various Gate Shapes in CMOS Image Sensor. ITE Transactions on Media Technology and Applications, 2018, 6, 163-170.	0.5	5
124	Plasma resistance of sintered and ion-plated yttrium oxyfluorides with various Y, O, and F composition ratios for use in plasma process chamber. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	2.1	5
125	Impact of Channel Direction Dependent Low Field Hole Mobility on (100) Orientation Silicon Surface. Japanese Journal of Applied Physics, 2011, 50, 04DC03.	1.5	5
126	Control of Nitrogen Depth Profile and Chemical Bonding State in Silicon Oxynitride Films Formed by Radical Nitridation. Japanese Journal of Applied Physics, 2005, 44, 7395-7399.	1.5	4

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127	Examination of degradation mechanism due to negative bias temperature stress from a perspective of hole energy for accurate lifetime prediction. Microelectronics Reliability, 2007, 47, 409-418.	1.7	4
128	NBTI Mechanism Based on Hole-Injection for Accurate Lifetime Prediction. ECS Transactions, 2007, 6, 229-243.	0.5	4
129	Circuit level prediction of device performance degradation due to negative bias temperature stress. Microelectronics Reliability, 2007, 47, 930-936.	1.7	4
130	Accurate negative bias temperature instability lifetime prediction based on hole injection. Microelectronics Reliability, 2008, 48, 1649-1654.	1.7	4
131	Effects of Ion-Bombardment-Assist and High Temperature on Growth of Zinc Oxide Films by Microwave Excited High Density Plasma Enhanced Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2009, 48, 04C135.	1.5	4
132	Very High Performance CMOS on Si(551) Surface using Radical Oxidation Silicon Flattening Technology and Accumulation-mode SOI Device Structure. ECS Transactions, 2009, 25, 115-129.	0.5	4
133	UV-Raman Spectroscopy Study on SiO2/Si Interface. ECS Transactions, 2009, 19, 55-66.	0.5	4
134	Inductively coupled plasma generator for an environmentally benign perfluorocarbon abatement system. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2009, 27, 465-470.	2.1	4
135	Data Analysis Technique of Atomic Force Microscopy for Atomically Flat Silicon Surfaces. IEICE Transactions on Electronics, 2009, E92-C, 664-670.	0.6	4
136	Ultra-low series resistance W/ErSi<inf>2</inf>/n⁺-Si and W/Pd<inf>2</inf>Si/p⁺-Si S/D electrodes for advanced CMOS platform. , 2010, , .		4
137	High-Rate Deposition of Amorphous Silicon Films by Microwave-Excited High-Density Plasma. Japanese Journal of Applied Physics, 2011, 50, 036502.	1.5	4
138	Impact of Channel Direction Dependent Low Field Hole Mobility on (100) Orientation Silicon Surface. Japanese Journal of Applied Physics, 2011, 50, 04DC03.	1.5	4
139	(Invited) High Power Normally-Off GaN MOSFET. ECS Transactions, 2011, 41, 87-100.	0.5	4
140	Recovery Characteristics of Anomalous Stress-Induced Leakage Current of 5.6 nm Oxide Films. Japanese Journal of Applied Physics, 2012, 51, 04DC02.	1.5	4
141	The role of the temperature on the scattering mechanisms limiting the electron mobility in metal-oxide-semiconductor field-effect-transistors fabricated on (110) silicon-oriented wafers. , 2012, , .		4
142	High-speed and highly accurate evaluation of electrical characteristics in MOSFETs. , 2013, , .		4
143	Hole-Trapping Process at Al2O3/GaN Interface Formed by Atomic Layer Deposition. IEEE Electron Device Letters, 2017, 38, 1309-1312.	3.9	4
144	Effect of drain current on appearance probability and amplitude of random telegraph noise in low-noise CMOS image sensors. Japanese Journal of Applied Physics, 2018, 57, 04FF08.	1.5	4

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145	[Papers] Impacts of Random Telegraph Noise with Various Time Constants and Number of States in Temporal Noise of CMOS Image Sensors. ITE Transactions on Media Technology and Applications, 2018, 6, 171-179.	0.5	4
146	Control of ion-flux and ion-energy in direct inductively coupled plasma reactor for interfacial-mixing plasma-enhanced atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, 032408.	2.1	4
147	High Integrity SiO2Gate Insulator Formed by Microwave-Excited Plasma Enhanced Chemical Vapor Deposition for AlGaN/GaN Hybrid Metalâ€“Oxideâ€“Semiconductor Heterojunction Field-Effect Transistor on Si Substrate. Japanese Journal of Applied Physics, 2012, 51, 04DF03.	1.5	4
148	High Performance 0.2 Âµm Dual Gate Complementary MOS Technologies by Suppression of Transient-Enhanced-Diffusion using Rapid Thermal Annealing. Japanese Journal of Applied Physics, 1998, 37, 1054-1058.	1.5	3
149	Saturation Phenomenon of Stress-Induced Gate Leakage Current. Japanese Journal of Applied Physics, 2002, 41, 2335-2338.	1.5	3
150	Reliability of silicon nitride gate dielectrics grown at 400 Â°C formed by microwave-excited high-density plasma. Applied Surface Science, 2003, 216, 246-251.	6.1	3
151	Oxygen radical treatment applied to ferroelectric thin films. Applied Surface Science, 2003, 216, 239-245.	6.1	3
152	A Low-Dielectric-Constant Sr2(Ta1-x,Nbx)2O7Thin Film Controlling the Crystal Orientation on an IrO2Substrate for One-Transistor-Type Ferroelectric Memory Device. Japanese Journal of Applied Physics, 2004, 43, 2194-2198.	1.5	3
153	Relationship between Sr2(Ta1-x,Nbx)2O7Crystal Phase and RF-Sputtering Plasma Condition for Metalâ€“Ferroelectricâ€“Insulatorâ€“Si Structure Device Formation. Japanese Journal of Applied Physics, 2006, 45, 3207-3212.	1.5	3
154	Control of Nitrogen Depth Profile near Silicon Oxynitride/Si(100) Interface Formed by Radical Nitridation. Japanese Journal of Applied Physics, 2006, 45, 6203-6209.	1.5	3
155	Accurate Circuit Performance Prediction Model and Lifetime Prediction Method of NBT Stressed Devices for Highly Reliable ULSI Circuits. , 2006, , .		3
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